

Device Modeling Report

COMPONENTS:
DIODE/ ENHANCED POWER LED / STANDARD
PART NUMBER: EP204K-35G1R1B1-CA
MANUFACTURER: PARA Light
EMARK: 25 degree C
COLER: Green

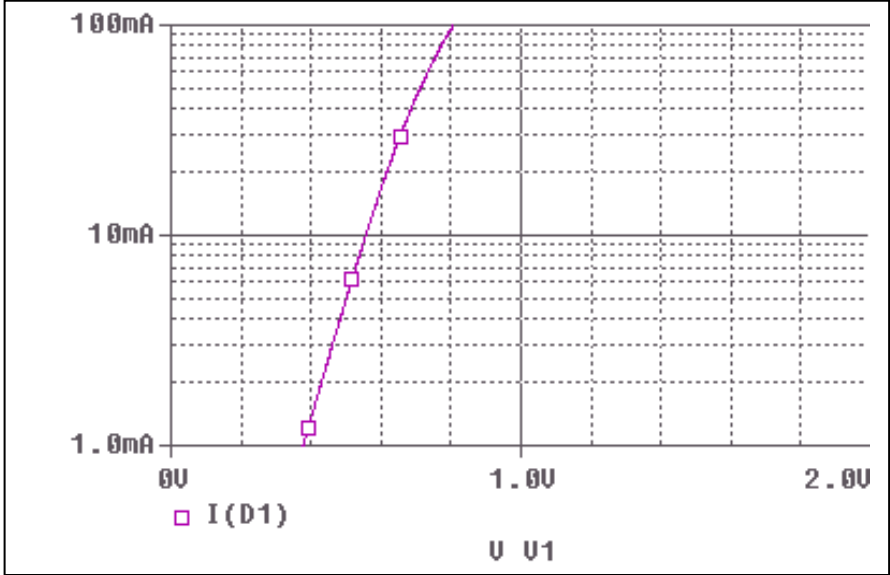


Bee Technologies Inc.

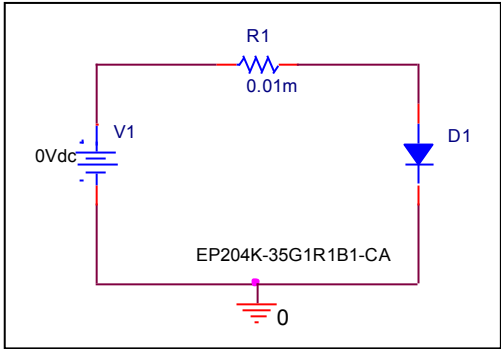
PSpice model parameter	Model description
IS	Saturation Current
N	Emission Coefficient
RS	Series Resistance
IKF	High-injection Knee Current
CJO	Zero-bias Junction Capacitance
M	Junction Grading Coefficient
VJ	Junction Potential
ISR	Recombination Current Saturation Value
BV	Reverse Breakdown Voltage(a positive value)
IBV	Reverse Breakdown Current(a positive value)
TT	Transit Time
EG	Energy-band Gap

Forward Current Characteristic

Circuit Simulation Result

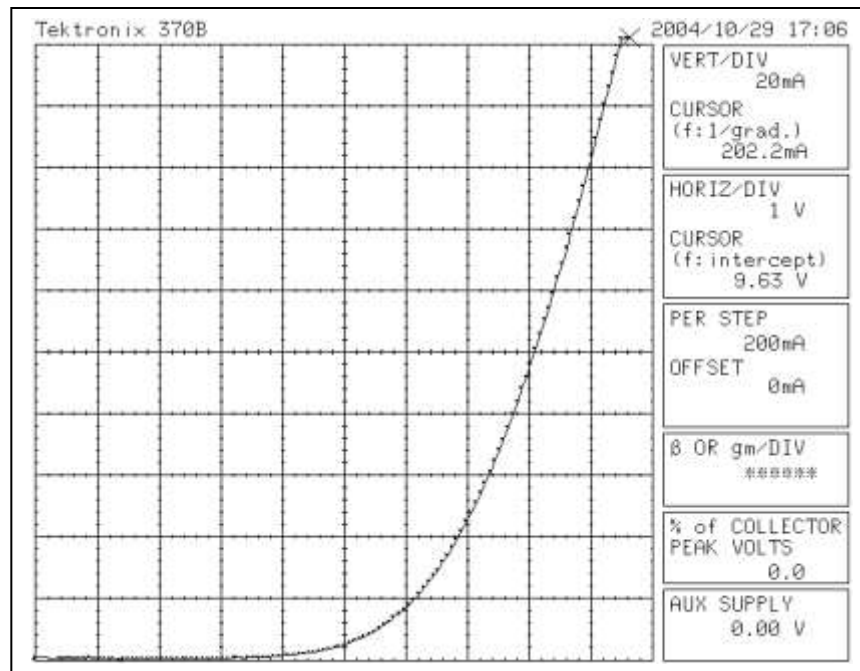


Evaluation Circuit



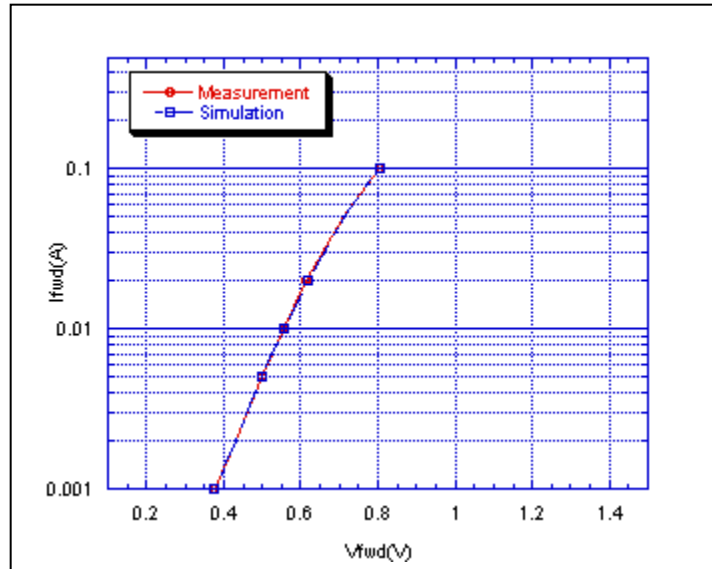
Forward Current Characteristic

Reference



Comparison Graph

Circuit Simulation Result

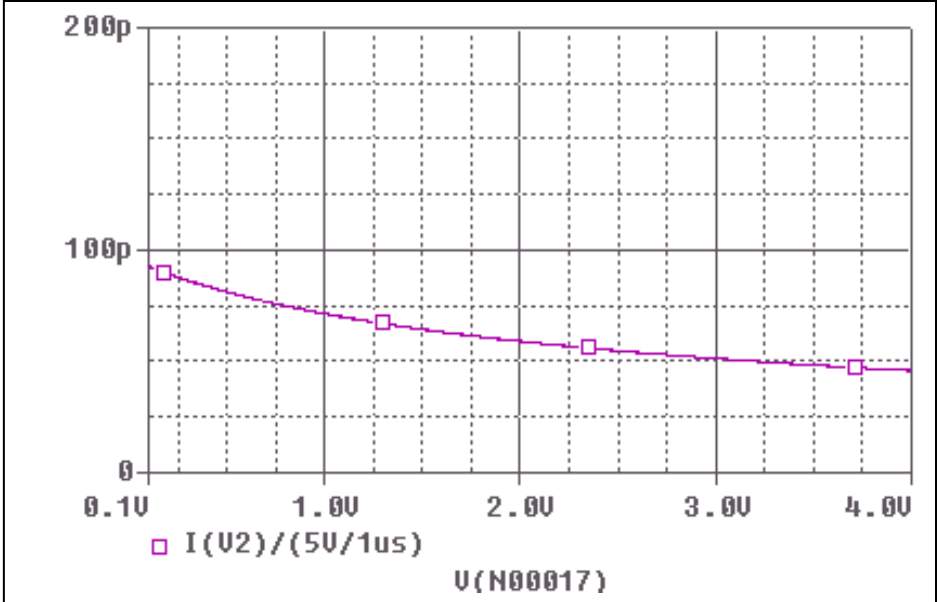


Simulation Result

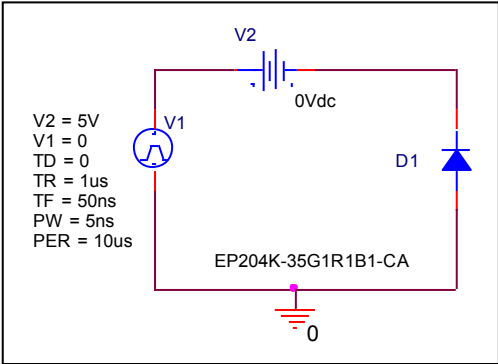
I_{fwd} (A)	V_{fwd} (V) Measurement	V_{fwd} (V) Simulation	%Error
0.001	0.375	0.377	0.533
0.002	0.434	0.4341	0.023
0.005	0.5	0.5	0
0.01	0.556	0.5564	0.071
0.02	0.616	0.6167	0.113
0.05	0.712	0.7114	0.084
0.1	0.807	0.8072	0.024

Capacitance Characteristic

Circuit Simulation Result

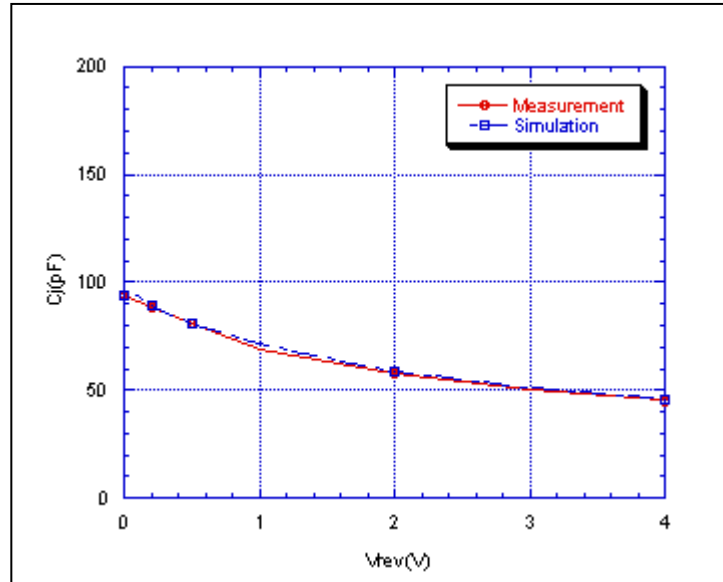


Evaluation Circuit



Comparison Graph

Circuit Simulation Result

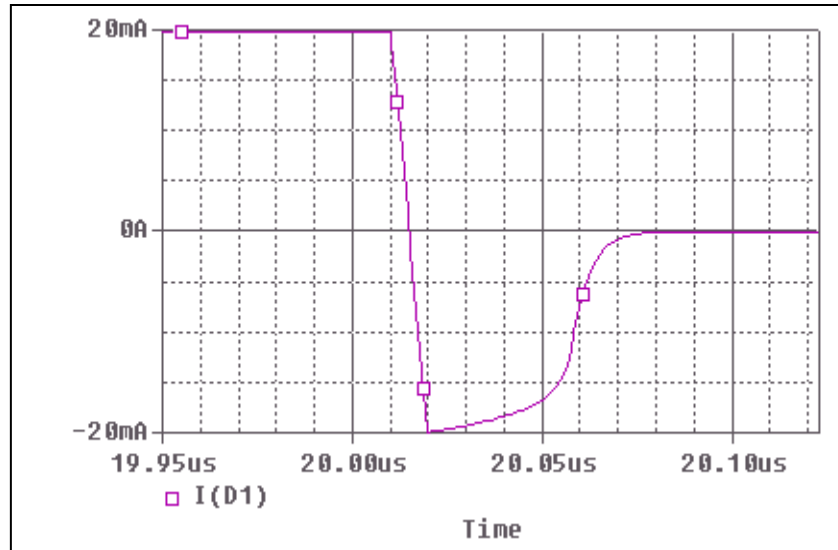


Simulation Result

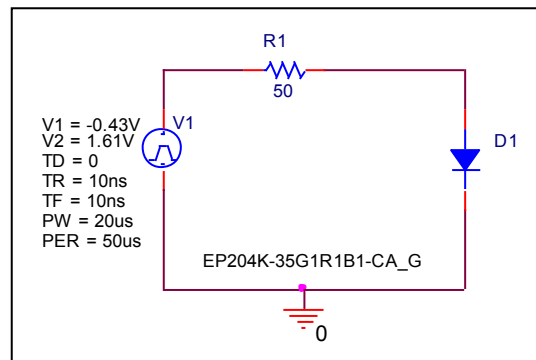
Vrev(V)	Cj(pF) Measurement	Cj(pF) Simulation	%Error
0	94	94	0
0.1	91.54	93.473	2.111
0.2	88.71	89.473	0.860
0.5	81.37	81.286	0.103
1	68.6	71.507	4.237
2	57.7	59.046	2.332
3	50	51.336	2.672
4	45	45.849	1.886

Reverse Recovery Characteristic

Circuit Simulation Result



Evaluation Circuit

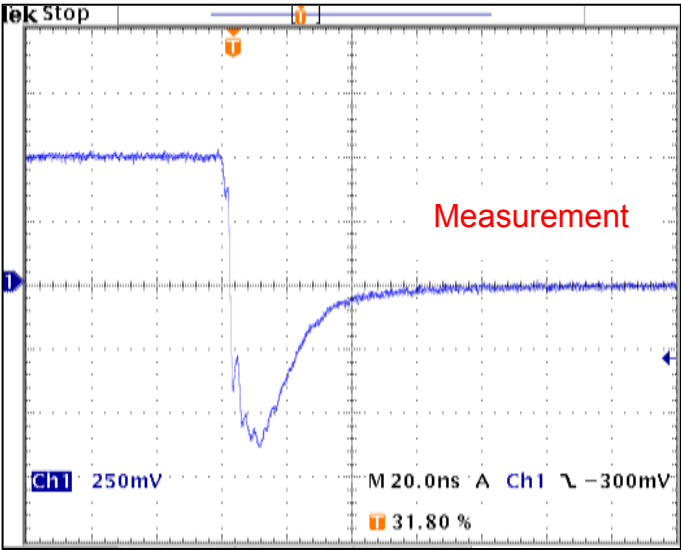


Compare Measurement vs. Simulation

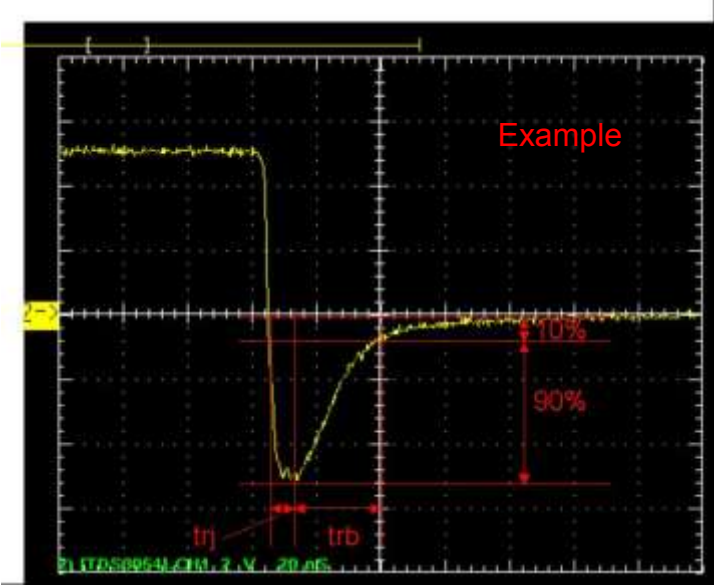
Symbol	Measurement	Unit	Simulation	Unit	%Error
$T_{rr}=t_{rj}+t_{rb}$	37.2	ns	37.4	ns	0.537

Reverse Recovery Characteristic

Reference



$T_{rj} = 9.20(\text{ns})$
 $T_{rb} = 28.0(\text{ns})$
Conditions: $I_{fwd} = I_{rev} = 0.2(\text{A})$, $R_I = 50$



Relation between t_{rj} and t_{rb}